



USG15R105HV

Preliminary

POWER MOSFET

N-CHANNEL SGT ENHANCEMENT POWER MOSFET

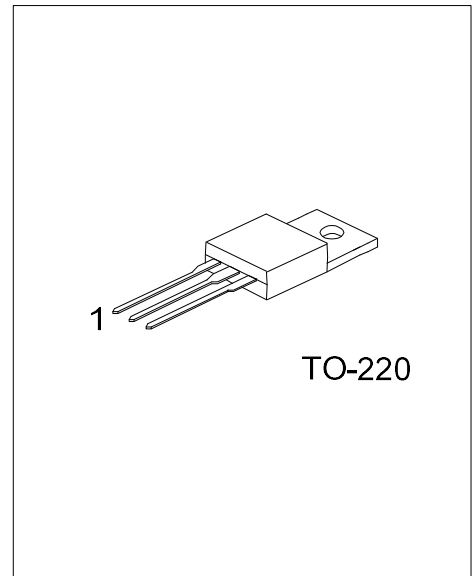
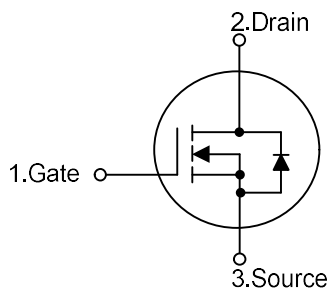
DESCRIPTION

The UTC **USG15R105HV** is a N-channel Power MOSFET, it uses UTC's advanced technology to provide the customers with low $R_{DS(ON)}$ characteristic by high cell density trench technology.

FEATURES

- * $R_{DS(ON)} \leq 10.5 \text{ m}\Omega$ @ $V_{GS} = 10\text{V}$, $I_D = 50\text{A}$
- * Extremely low on-resistance $R_{DS(ON)}$
- * Excellent Low Ciss

SYMBOL



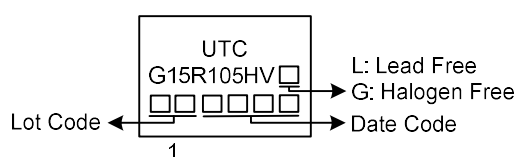
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
USG15R105HVL-TA3-T	USG15R105HVG-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

USG15R105HVG-TA3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TA3: TO-220
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATING (T_C = 25°C, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	150	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current	DC	I _D	80	A
	Pulsed (Note 2)	I _{DM}	160	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	29	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.4	V/ns
Power Dissipation		P _D	180	W
Junction Temperature		T _J	+150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. L = 0.1mH, I_{AS} = 24.3A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C

4. I_{SD} ≤ 30A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	62.5	°C/W
Junction to Case	θ _{JC}	0.69	°C/W

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

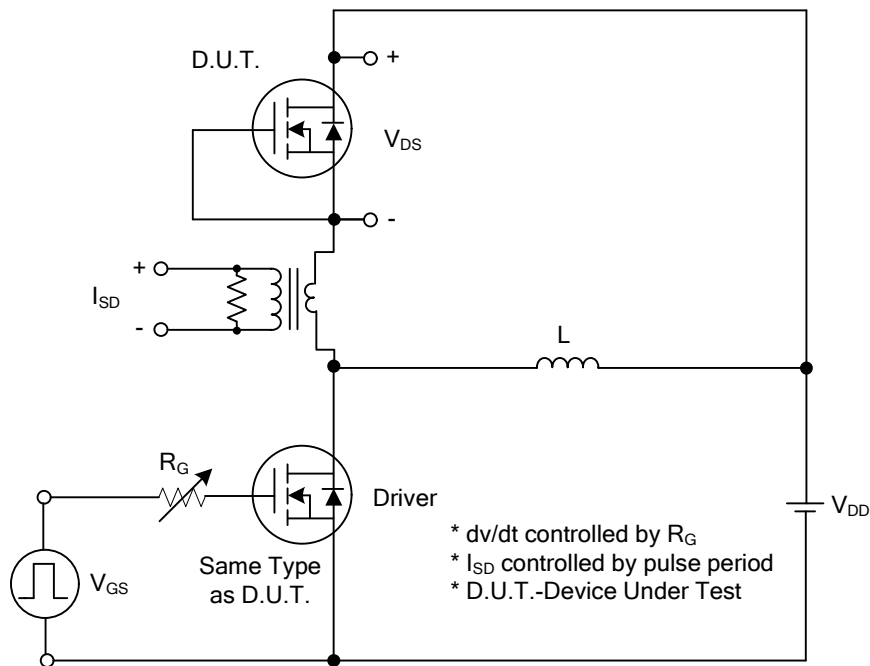
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified.)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	150			V
Drain-Source Leakage Current		I _{DSS}	V _D =150V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _D =0V			+100	nA
	Reverse		V _{GS} =-20V, V _D =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _D = V _{GS} , I _D =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =20A			10.5	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _D =25V, f=1.0MHz		6613		pF
Output Capacitance		C _{OSS}			1281		pF
Reverse Transfer Capacitance		C _{RSS}			122		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _D =120V, V _{GS} =10V, I _D =80A (Note 1, 2)		122		nC
Gate to Source Charge		Q _{GS}			49		nC
Gate to Drain Charge		Q _{GD}			35		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =75V, V _{GS} =10V, I _D =80A, R _G =25Ω (Note 1, 2)		130		ns
Rise Time		t _R			82		ns
Turn-OFF Delay Time		t _{D(OFF)}			241		ns
Fall-Time		t _F			49		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				80	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				160	A
Diode Forward Voltage		V _{SD}	I _F =80A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =30A, V _{GS} =0V,		88		nS
Reverse Recovery Charge		Q _{rr}	dI _F /dt =100A/μs		289		nC

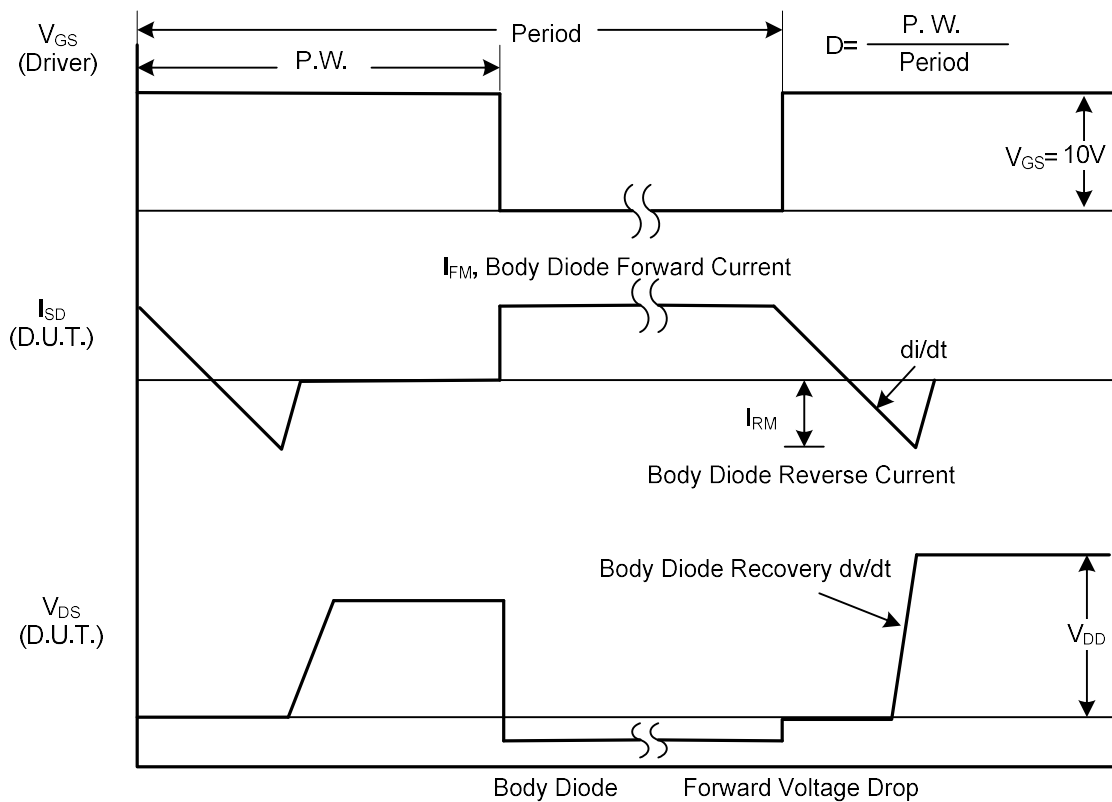
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

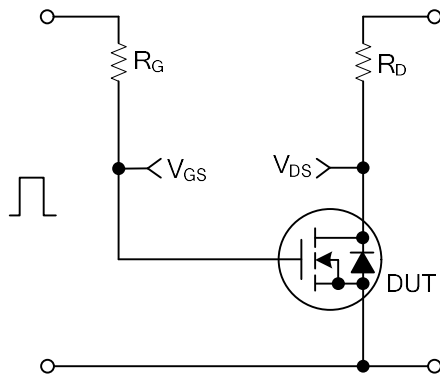


Peak Diode Recovery dv/dt Test Circuit

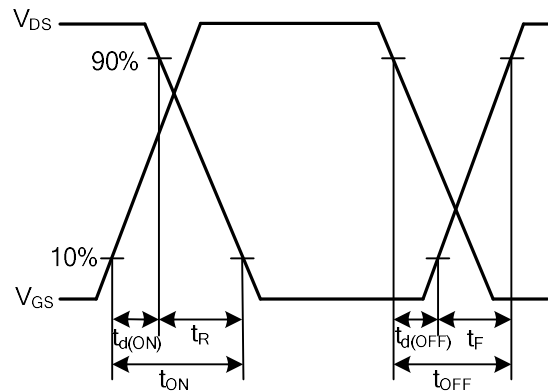


Peak Diode Recovery dv/dt Waveforms

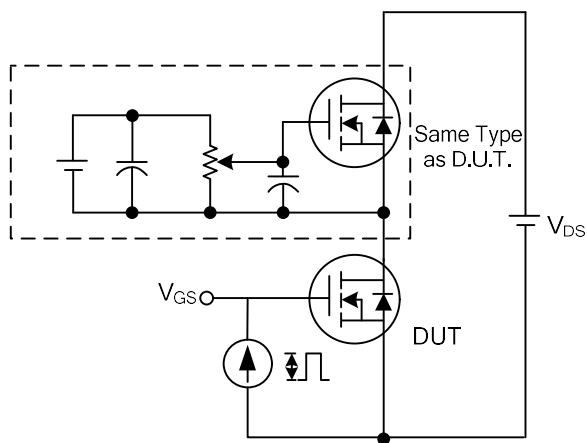
■ TEST CIRCUITS AND WAVEFORMS



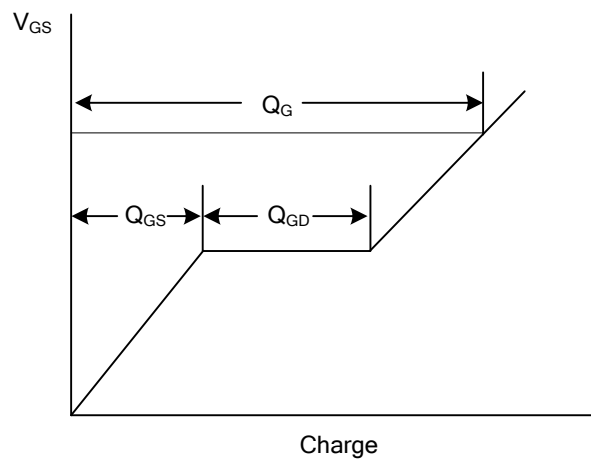
Switching Test Circuit



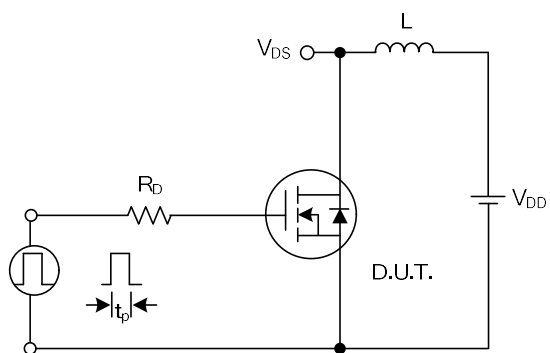
Switching Waveforms



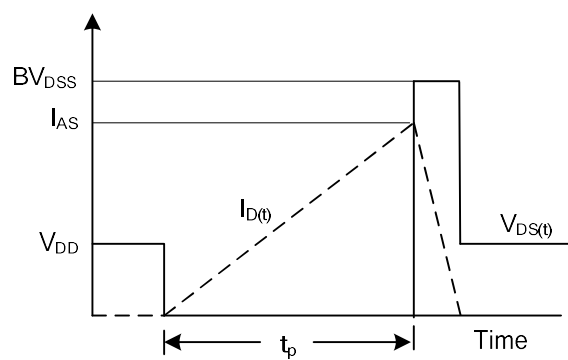
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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